

Docket No.: 67161-039

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hideto HIDAKA

Serial No.: 10/615,777

Filed: July 10, 2003

For: SEMICONDUCTOR MEMORY DEVICE WITH MAGNETIC DISTURBANCE REDUCED

: Customer Number: 20277
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: Confirmation Number: 9486
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: Group Art Unit: 2811
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: Examiner: To be Assigned
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

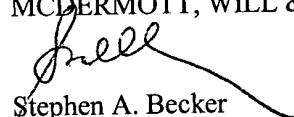
Dear Sir:

This Information Disclosure Statement and 1449 Form is supplemental to that filed July 10, 2003. The reason for this supplemental Information Disclosure Statement and 1449 Form is to correct a typographical error made on the initial 1449 Form.. The last listed Prior Art Publication year was initially filed as 2000. The year should be changed to read **2001** as indicated on attached copies.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY


Stephen A. Becker
Registration No. 26,527

600 13th Street, N.W.
Washington, DC 20005-3096
(202) 756-8000 SAB:mcw
Facsimile: (202) 756-8087
Date: October 20, 2003



SHEET 1 OF 1

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

(PTO-1449)

ATTY. DOCKET NO.
67161-039SERIAL NO.
10/615,777APPLICANT
Hideto HIDAKAFILING DATE
July 10, 2003GROUP
2811

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Documt Number Number-Kind Code2 (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	US 2002/0172073	11/21/2002	HIDAKA	
		US 10/327,888	12/26/2002	HIDAKA	
		US			
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 2002-170375	06/14/2002	HIRAI		abstract	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		SCHEUERLEIN, et al. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell" IEEE International Solid-State Circuits Conference (2000) TA 7.2
		DURLAM, et al. "Nonvolatile RAM Based on Magnetic Tunnel Junction Elements" IEEE International Solid-State Circuits Conference (2000) TA 7.3
		NAJI, et al. "A 256kb 3.0V 1T1MJT Nonvolatile Magnetoresistive RAM" IEEE International Solid-State Circuits Conference (2001) TA 7.6

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.
1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.